

## Plastic-Encapsulate Transistors

DUAL TRANSISTOR (PNP+PNP)

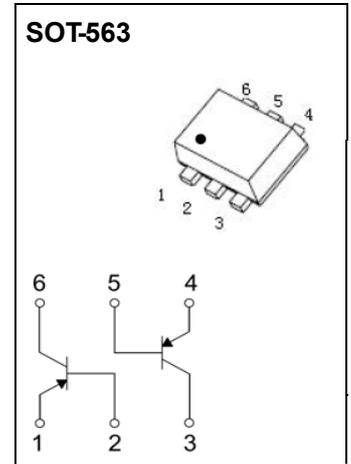
### FEATURES

- Complementary to MMDT5551DW
- Small Surface Mount Package
- Ideal for Medium Power Amplification and Switching

MARKING: 2L

### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	-160	V
$V_{CEO}$	Collector-Emitter Voltage	-150	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-600	mA
$P_C$	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^\circ\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^\circ\text{C}$



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=-100\mu\text{A}$ , $I_E=0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$ , $I_B=0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}$ , $I_C=0$	-5			V
Collector cut-off current	$I_{CB0}$	$V_{CB}=-120\text{V}$ , $I_E=0$			-50	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-3\text{V}$ , $I_C=0$			-50	nA
DC current gain	$h_{FE}$	$V_{CE}=-5\text{V}$ , $I_C=-1\text{mA}$	50			
		$V_{CE}=-5\text{V}$ , $I_C=-10\text{mA}$	60		300	
		$V_{CE}=-5\text{V}$ , $I_C=-50\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}$ , $I_B=-5\text{mA}$			-0.5	V
		$I_C=-10\text{mA}$ , $I_B=-1\text{mA}$			-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-50\text{mA}$ , $I_B=-5\text{mA}$			-1	V
		$I_C=-10\text{mA}$ , $I_B=-1\text{mA}$			-1	V
Transition frequency	$f_T$	$V_{CE}=-10\text{V}$ , $I_C=-10\text{mA}$ , $f=100\text{MHz}$	100			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10\text{V}$ , $I_E=0$ , $f=1\text{MHz}$			6	pF

## Typical Characteristics

Static Characteristic

